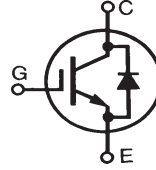


# High Voltage IGBT with Diode

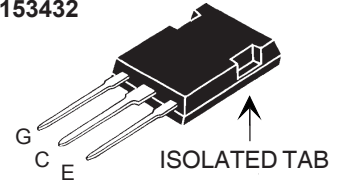
## IXGR 32N170AH1

Electrically Isolated Tab



$$\begin{aligned}
 V_{CES} &= 1700 \text{ V} \\
 I_{C25} &= 26 \text{ A} \\
 V_{CE(sat)} &= 5.2 \text{ V} \\
 t_{fi(typ)} &= 50 \text{ ns}
 \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1700	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1 \text{ M}\Omega$	1700	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	26	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	17	A
$I_{F90}$		14	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1 ms	200	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15 \text{ V}$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 5\Omega$ Clamped inductive load	$I_{CM} = 70$ @ $0.8 V_{CES}$	A
$t_{sc}$	$T_J = 125^\circ\text{C}$ , $V_{CE} = 1200 \text{ V}$ ; $V_{GE} = 15 \text{ V}$ , $R_G = 10\Omega$	10	$\mu\text{s}$
$P_C$	$T_C = 25^\circ\text{C}$	200	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$F_C$	Mounting force with clamp	22...130/5...30	N/lb
$V_{ISOL}$	50/60 Hz, 1 minute	2500	~V
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
<b>Weight</b>		5	g

 ISOPLUS247 (IXGR)  
E153432

 G = Gate,  
E = Emitter

C = Collector,

### Features

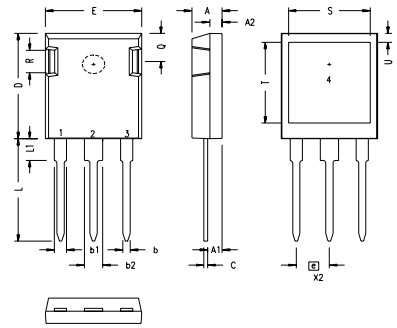
- Electrically isolated tab
- High current handling capability
- MOS Gate turn-on  
- drive simplicity
- Rugged NPT structure
- Molding epoxies meet UL 94 V-0 flammability classification

### Applications

- Capacitor discharge & pulser circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 1 \text{ mA}$ , $V_{GE} = 0 \text{ V}$	1700		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$ , $V_{CE} = V_{GE}$	3.0		V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$ Note 1 $T_J = 125^\circ\text{C}$			500 $\mu\text{A}$ 8 mA
$I_{GES}$	$V_{CE} = 0 \text{ V}$ , $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$ $T_J = 125^\circ\text{C}$	4.2 4.8	5.2	V V

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$I_C = I_{C25}; V_{CE} = 10\text{ V}$ Note 2	25	33	S
$C_{ies}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		3700	pF
$C_{oes}$			180	pF
$C_{res}$			44	pF
$Q_g$	$I_C = I_{C90}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		155	nC
$Q_{ge}$			30	nC
$Q_{gc}$			51	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C90}, V_{GE} = 15\text{ V}$ $R_G = 2.7\ \Omega, V_{CE} = 0.8 V_{CES}$ Note 3		46	ns
$t_{ri}$			57	ns
$t_{d(off)}$			270	500 ns
$t_{fi}$			50	100 ns
$E_{off}$			1.5	3.0 mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C90}, V_{GE} = 15\text{ V}$ $R_G = 2.7\ \Omega, V_{CE} = 0.8 V_{CES}$ Note 3		48	ns
$t_{ri}$			42	ns
$E_{on}$			2.5	mJ
$t_{d(off)}$			300	ns
$t_{fi}$			70	ns
$E_{off}$		2.4	mJ	
$R_{thJC}$				0.65 K/W
$R_{thCK}$		0.15		K/W

**ISOPLUS247 Outline**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - NO CONNECTION

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

**See IXGX32N170AH1 for characteristic curves**

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = 20\text{ A}, V_{GE} = 0\text{ V}$ , Note 2		2.7	V
$I_{RM}$	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}, -di_F/dt = 800\text{ A}/\mu\text{s}$ $V_R = 600\text{ V}$		50	A
$t_{rr}$			150	ns
$R_{thJC}$				1.5 K/W

- Notes: 1. Device must be heatsunk for high temperature leakage current measurements to avoid thermal runaway.
2. Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$
3. Switching times may increase for  $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$ , higher  $T_J$  or increased  $R_G$ .
4. See DH60-18A and IXGH32N170A datasheets for additional characteristics

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	